

COPY

SHEET 1 OF 1

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.164P (DV)	APPLICATION NO. 40721790 Unknown 10/618, 524
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Gilton, Terry L.	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE April 10, 2002 July 14, 2003	GROUP 490 Unknown 2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
Lee	5,761,115	6/2/1998	Kozicki, et al.				
Lee	5,896,312	4/20/1999	Kozicki, et al.				
Lee	5,914,893	6/22/1999	Kozicki, et al.				
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FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
Lee	WO 00/48196	08/17/00	WO				
Lee	WO 02/21542 A1	03/14/02	WO				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	P. Boolchand, et al., "Mobile Silver Ions and Glass Formation in Solid Electrolytes" <u>Nature</u> , Vol. 410, April 2001, pp. 1070-1073
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MSO-3145.DOC:afa
070902

EXAMINER <i>Karen Mary Lee</i>	DATE CONSIDERED <i>2/12/04</i>
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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON 164101	APPLICATION NO. 10421-790 <i>Unknown</i> 10/618,824
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT Gilton, Terry L.	
(USE SEVERAL SHEETS IF NECESSARY)		FILING DATE April 10, 2002 July 14, 2003	GROUP 2010 <i>Unknown</i> 2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
<i>Lee</i>		6,348,365	02/19/02	Moore, et al.			
<i>Lee</i>		6,418,040	07/09/02	Kozicki, et al.			

FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)						

MSO-3448.DOC:afa
090602

EXAMINER <i>Lee Mary Lee</i>	DATE CONSIDERED <i>2/2/04</i>
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SHEET 1 OF 1

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. MICRON.1648A1	APPLICATION NO. 10/421,790 <i>Unknown</i> 10/618,824
APPLICANT Gilton, Terry L.		FILING DATE April 10, 2002 <i>July 14, 2003</i>
GROUP 28TB <i>Unknown</i>		2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)	
<i>Lee</i> <div style="border-left: 1px solid black; height: 100px; margin: 0 auto; width: 20px;"></div>	6,487,106	11/26/02	Kozicki				
	2002/0168820	11/14/02	Kozicki, et al.				
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FOREIGN PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

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EXAMINER <i>Kevin Ming Lee</i>	DATE CONSIDERED <i>2/12/04</i>
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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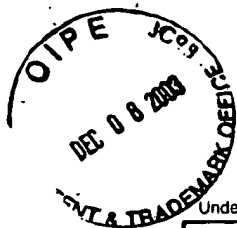
Complete if Known

Application Number	10/618,824
Filing Date	July 14, 2003
First Named Inventor	Terry L. Gilton
Art Unit	N/A 2823
Examiner Name	Not Yet Assigned H. Lee
Attorney Docket Number	M4065.1006/P1006-A

Sheet 1 of 12

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
* [initials]	AA	2002/0000666	1/2002	Kozicki et al.	
*	AB	2002/0072188	6/2002	Gilton	
* [initials]	AC	2002/0106849	08/2002	Moore	
*	AD	2002/0123169	09/2002	Moore et al.	
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*	AH	2002/0132417	09/2002	Li	
*	AI	2002/0160551	10/2002	Harshfield	
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				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A-2823
				Examiner Name	Not Yet Assigned H. Lee
Sheet	2	of	12	Attorney Docket Number	M4065.1006/P1006-A

Lee	AS1	4,320,191	3/1982	Yoshikawa et al.	
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				Application Number	10/618,824
				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	N/A- 2823
				Examiner Name	Not Yet Assigned H. Lee
Sheet	4	of	12	Attorney Docket Number	M4065.1006/P1006-A

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	†
		Country Code ² -Number ³ -Kind Code ⁴ (if known)					
	BA	JP-56126916		10/1981	Akira et al.		
	BB	WO 97/48032		12/18/1997	Kozicki et al.		
	BC	WO 99/28914		06/10/1999	Kozicki et al.		

Examiner Signature	<i>Kevin Ming Lee</i>	Date Considered	2/12/04
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		Application Number	10/618,824		
		Filing Date	July 14, 2003		
		First Named Inventor	Terry L. Gilton		
		Group Art Unit	N/A 2823		
		Examiner Name	Not Yet Assigned H. Lee		
Sheet	5	of	12	Attorney Docket Number	M4065.1006/P1006-A

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
Lee	CA	Abdel-Ali, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge5As38Te57 chalcogenide glass, Vacuum 59 (2000) 845-853.		
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	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.		
	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se75Ge25-xSbx, Appl. Phys. A 55 (1992) 167-169.		
	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe1-x, Egypt, J. Phys. 17 (1986) 335-342.		
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.		
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.		
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.		
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.		
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.		
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810		
	CL	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: Programmable Metalization Cell(PMC), pp. 1-6 (Pre-May 2000).		
	CM	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.		
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	CP	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.		
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PTO/SB/08B (10-01)

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U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/618,824
		Filing Date	July 14, 2003
		First Named Inventor	Terry L. Gilton
		Group Art Unit	HA 2823
		Examiner Name	Not Yet Assigned H. Lee
Sheet 6 of 12	Attorney Docket Number	M4065.1006/P1006-A	

not consider

✓	CW	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg4I5, Solid State Ionics 70/71 (1994) 72-76.
✓	CX	Boolchand, P., The maximum in glass transition temperature (Tg) near x=1/3 in GexSe1-x Glasses, Asian Journal of Physics (2000) 9, 709-72.
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		Examiner Name	Not Yet Assigned H. Lee		
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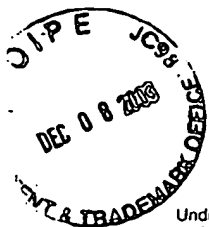
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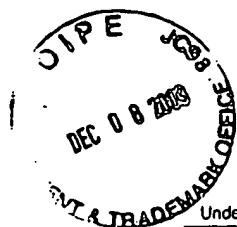
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Approved for use through 10/31/2002.OMB 0651-0031

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				Filing Date	July 14, 2003
				First Named Inventor	Terry L. Gilton
				Group Art Unit	NTA 2823
				Examiner Name	Not Yet Assigned H. Lee
				Attorney Docket Number	M4065.1006/P1006-A
Sheet	12	of	12		

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Examiner Signature	<i>Hees Mary Lee</i>	Date Considered	<i>2/2/54</i>
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